

# MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)



**ON Semiconductor®**

<http://onsemi.com>

## Complementary Power Transistors

### DPAK For Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

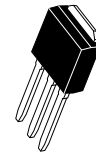
#### Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves
- Straight Lead Version in Plastic Sleeves (“1” Suffix)
- Lead Formed Version in 16 mm Tape and Reel (“T4” Suffix)
- Electrically Similar to Popular TIP31 and TIP32 Series
- Epoxy Meets UL 94, V-0 @ 0.125 in
- ESD Ratings:
  - ♦ Human Body Model, 3B > 8000 V
  - ♦ Machine Model, C > 400 V
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Packages\*

**SILICON  
POWER TRANSISTORS  
3 AMPERES  
40 AND 100 VOLTS  
15 WATTS**

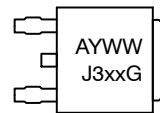


**DPAK  
CASE 369C  
STYLE 1**

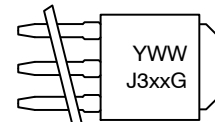


**DPAK-3  
CASE 369D  
STYLE 1**

#### MARKING DIAGRAMS



DPAK



DPAK-3

A = Site Code  
Y = Year  
WW = Work Week  
xx = 1, 1C, 2, or 2C  
G = Pb-Free Package

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 9 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,  
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

**MAXIMUM RATINGS**

| Rating  | Symbol         | Max           | Unit                     |
|---|----------------|---------------|--------------------------|
| Collector–Emitter Voltage<br>MJD31, NJVMJD31T4G, MJD32, NJVMJD32T4G<br>MJD31C, NJVMJD31CT4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G | $V_{CEO}$      | 40<br>100     | Vdc                      |
| Collector–Base Voltage<br>MJD31, NJVMJD31T4G, MJD32, NJVMJD32T4G<br>MJD31C, NJVMJD31CT4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G    | $V_{CB}$       | 40<br>100     | Vdc                      |
| Emitter–Base Voltage  | $V_{EB}$       | 5             | Vdc                      |
| Collector Current<br>Continuous<br>Peak   | $I_C$          | 3<br>5        | Adc                      |
| Base Current  | $I_B$          | 1             | Adc                      |
| Total Power Dissipation<br>@ $T_C = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$                                      | $P_D$          | 15<br>0.12    | W<br>W/ $^\circ\text{C}$ |
| Total Power Dissipation<br>@ $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$                                      | $P_D$          | 1.56<br>0.012 | W<br>W/ $^\circ\text{C}$ |
| Operating and Storage Junction Temperature Range  | $T_J, T_{stg}$ | -65 to +150   | $^\circ\text{C}$         |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

**THERMAL CHARACTERISTICS**

| Characteristic                           | Symbol          | Max | Unit                      |
|--|-----------------|-----|---------------------------|
| Thermal Resistance, Junction–to–Case     | $R_{\theta JC}$ | 8.3 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction–to–Ambient* | $R_{\theta JA}$ | 80  | $^\circ\text{C}/\text{W}$ |
| Lead Temperature for Soldering Purposes  | $T_L$           | 260 | $^\circ\text{C}$          |

\*These ratings are applicable when surface mounted on the minimum pad sizes recommended.

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,  
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|----------------|--------|-----|-----|------|
|----------------|--------|-----|-----|------|

**OFF CHARACTERISTICS**

|  |                |           |          |                 |
|--|----------------|-----------|----------|-----------------|
| Collector–Emitter Sustaining Voltage (Note 1)<br>( $I_C = 30\text{ mAdc}$ , $I_B = 0$ )<br>MJD31, NJVMJD31T4G, MJD32, NJVMJD32T4G<br>MJD31C, NJVMJD31CT4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G                          | $V_{CEO(sus)}$ | 40<br>100 | –<br>–   | Vdc             |
| Collector Cutoff Current<br>( $V_{CE} = 40\text{ Vdc}$ , $I_B = 0$ )<br>MJD31, NJVMJD31T4G, MJD32, NJVMJD32T4G<br>( $V_{CE} = 60\text{ Vdc}$ , $I_B = 0$ )<br>MJD31C, NJVMJD31CT4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G | $I_{CEO}$      | –<br>–    | 50<br>50 | $\mu\text{Adc}$ |
| Collector Cutoff Current<br>( $V_{CE} = \text{Rated } V_{CEO}$ , $V_{EB} = 0$ )  | ICES           | –         | 20       | $\mu\text{Adc}$ |
| Emitter Cutoff Current<br>( $V_{BE} = 5\text{ Vdc}$ , $I_C = 0$ )  | $I_{EBO}$      | –         | 1        | mAdc            |

**ON CHARACTERISTICS** (Note 1)

|   |               |          |         |     |
|---|---------------|----------|---------|-----|
| DC Current Gain<br>( $I_C = 1\text{ Adc}$ , $V_{CE} = 4\text{ Vdc}$ )<br>( $I_C = 3\text{ Adc}$ , $V_{CE} = 4\text{ Vdc}$ ) | $h_{FE}$      | 25<br>10 | –<br>50 |     |
| Collector–Emitter Saturation Voltage<br>( $I_C = 3\text{ Adc}$ , $I_B = 375\text{ mAdc}$ )                                  | $V_{CE(sat)}$ | –        | 1.2     | Vdc |
| Base–Emitter On Voltage<br>( $I_C = 3\text{ Adc}$ , $V_{CE} = 4\text{ Vdc}$ )   | $V_{BE(on)}$  | –        | 1.8     | Vdc |

**DYNAMIC CHARACTERISTICS**

|   |          |    |   |     |
|---|----------|----|---|-----|
| Current Gain – Bandwidth Product (Note 2)<br>( $I_C = 500\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f_{test} = 1\text{ MHz}$ ) | $f_T$    | 3  | – | MHz |
| Small–Signal Current Gain<br>( $I_C = 0.5\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1\text{ kHz}$ )                         | $h_{fe}$ | 20 | – |     |

1. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
2.  $f_T = |h_{fe}| \cdot f_{test}$ .

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

TYPICAL CHARACTERISTICS

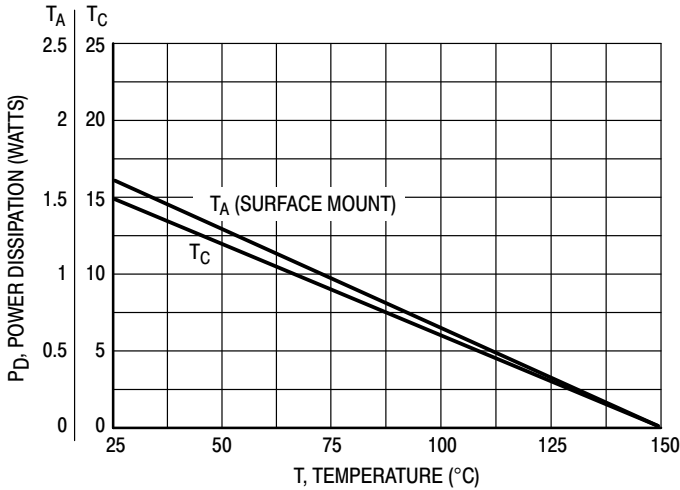
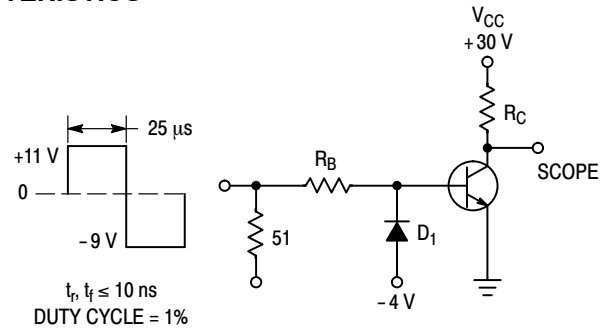


Figure 1. Power Derating



$R_B$  and  $R_C$  VARIED TO OBTAIN DESIRED CURRENT LEVELS  
 $D_1$  MUST BE FAST RECOVERY TYPE, e.g.:  
 1N5825 USED ABOVE  $I_B \approx 100$  mA  
 MSD6100 USED BELOW  $I_B \approx 100$  mA  
 REVERSE ALL POLARITIES FOR PNP.

Figure 2. Switching Time Test Circuit

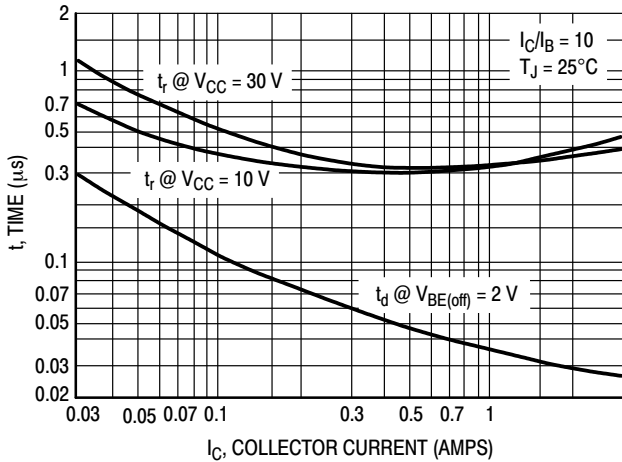


Figure 3. Turn-On Time

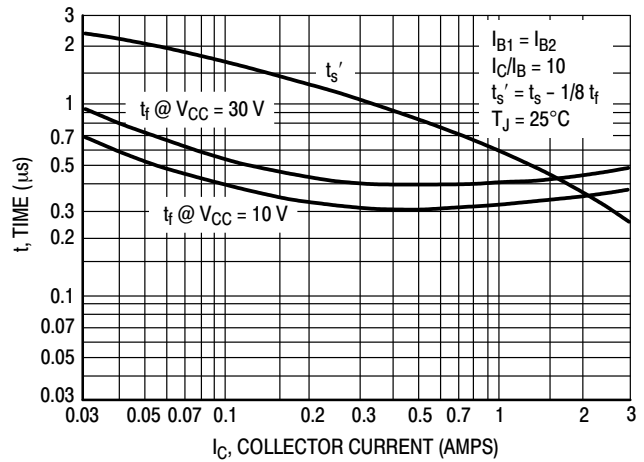


Figure 4. Turn-Off Time

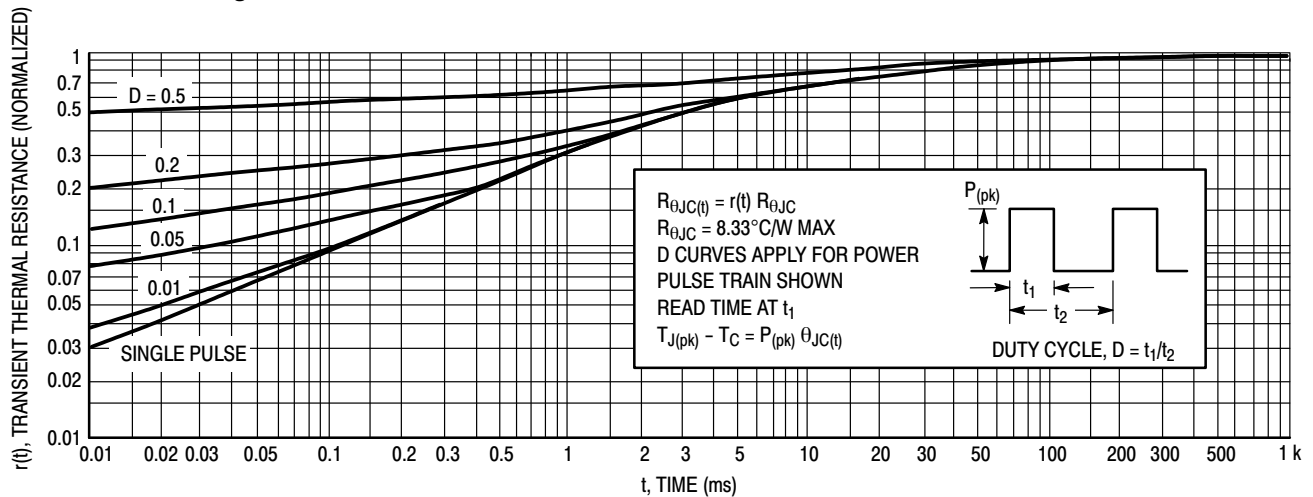


Figure 5. Thermal Response

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

TYPICAL CHARACTERISTICS – MJD31, MJD31C (NPN)

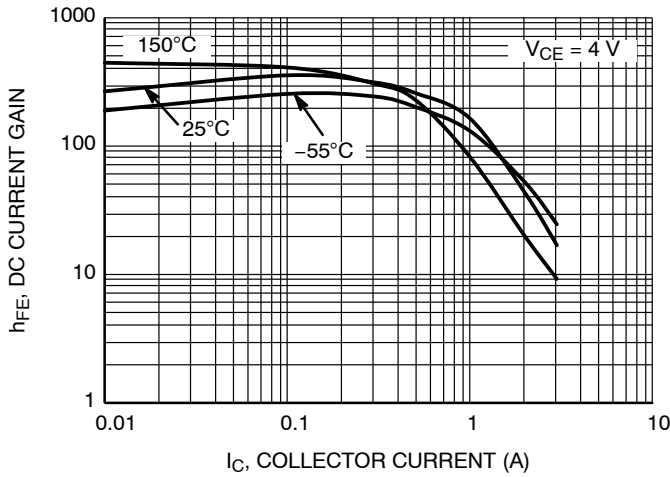


Figure 6. DC Current Gain at  $V_{CE} = 4\text{ V}$

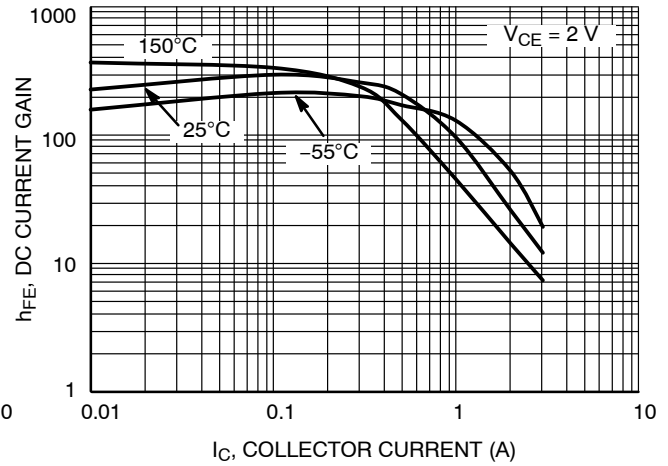


Figure 7. DC Current Gain at  $V_{CE} = 2\text{ V}$

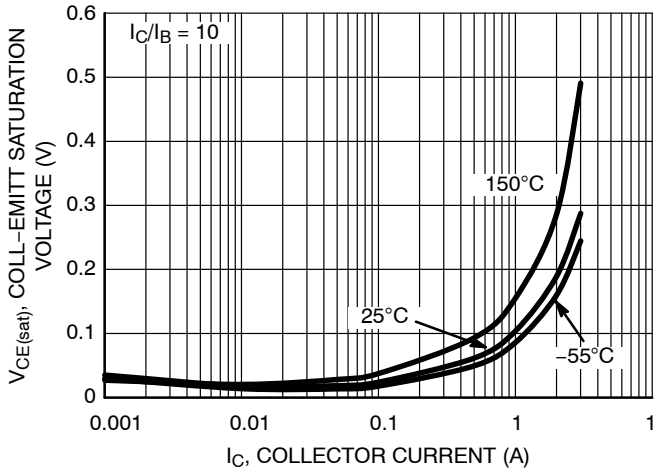


Figure 8. Collector-Emitter Saturation Voltage

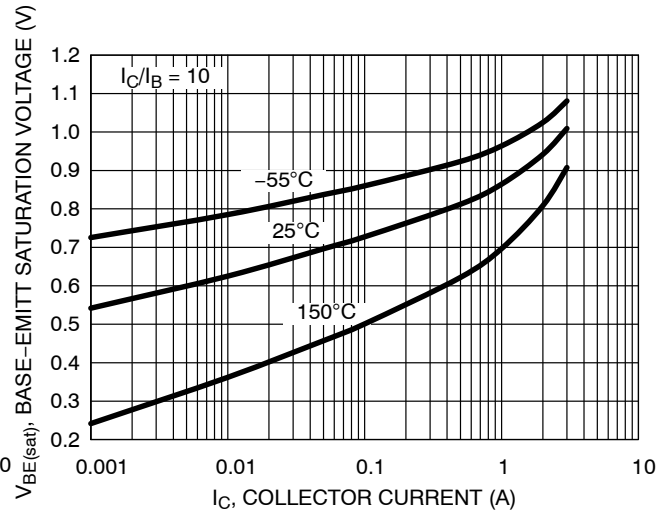


Figure 9. Base-Emitter Saturation Voltage

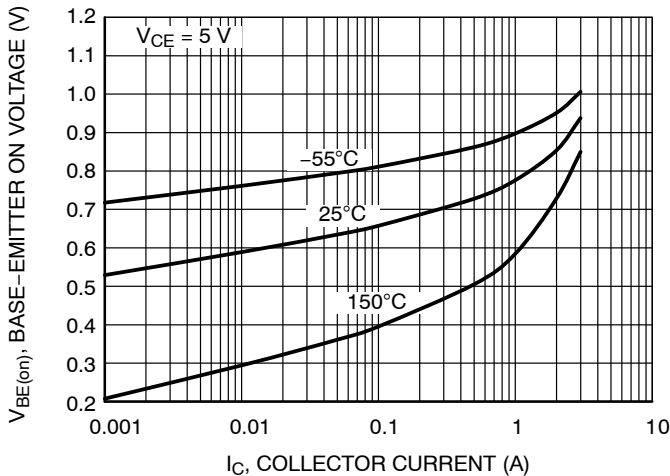


Figure 10. Base-Emitter "On" Voltage

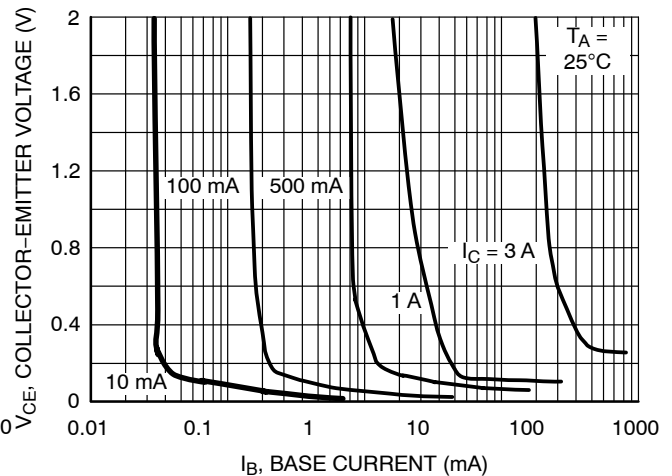


Figure 11. Collector Saturation Region

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,  
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)  
TYPICAL CHARACTERISTICS – MJD31, MJD31C (NPN)

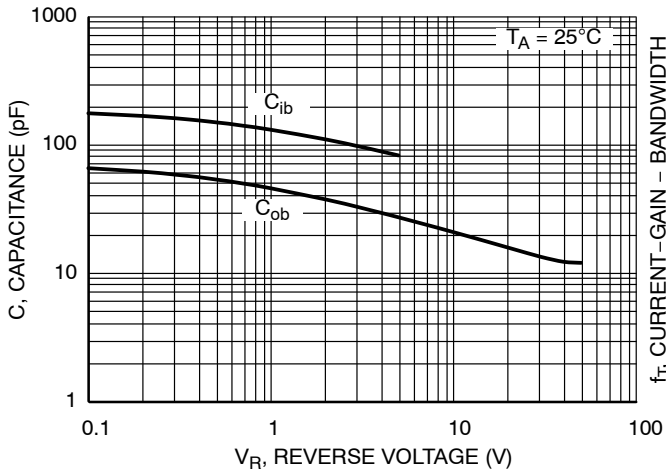


Figure 12. Capacitance

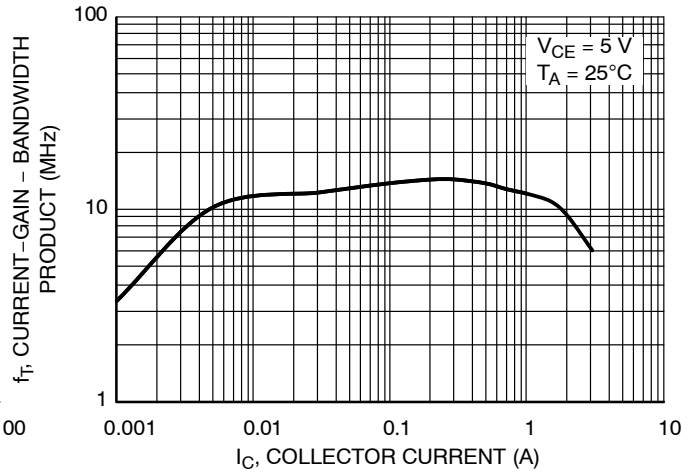


Figure 13. Current-Gain-Bandwidth Product

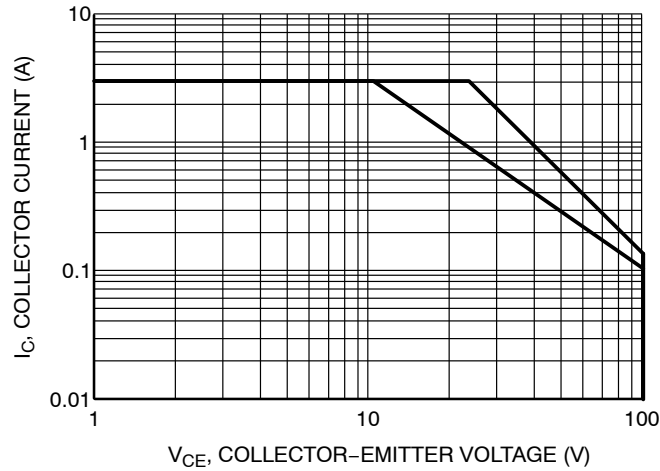


Figure 14. Safe Operating Area

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

TYPICAL CHARACTERISTICS – MJD32, MJD32C (PNP)

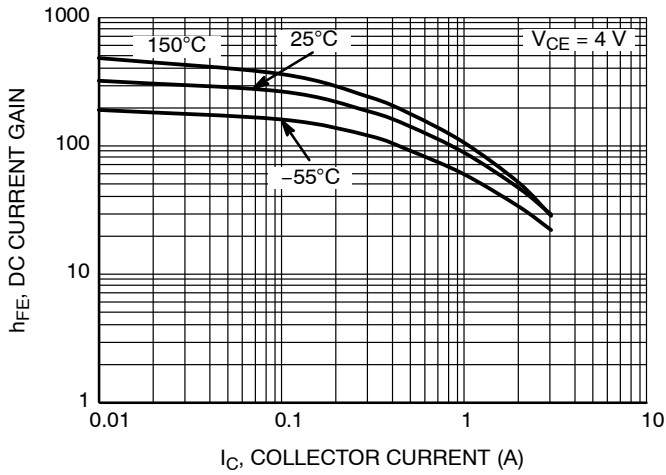


Figure 15. DC Current Gain at  $V_{CE} = 4\text{ V}$

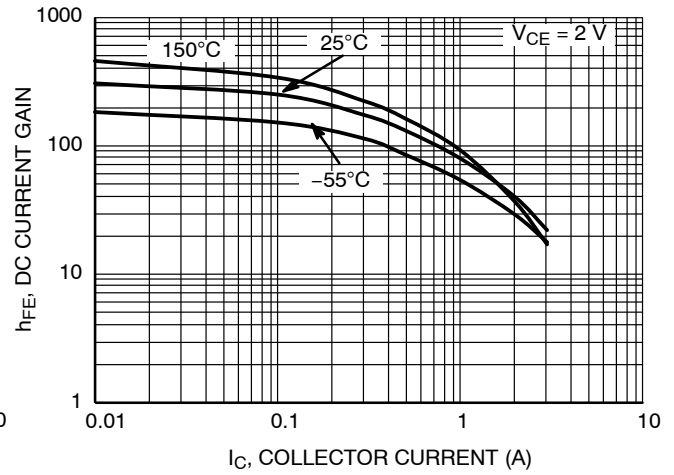


Figure 16. DC Current Gain at  $V_{CE} = 2\text{ V}$

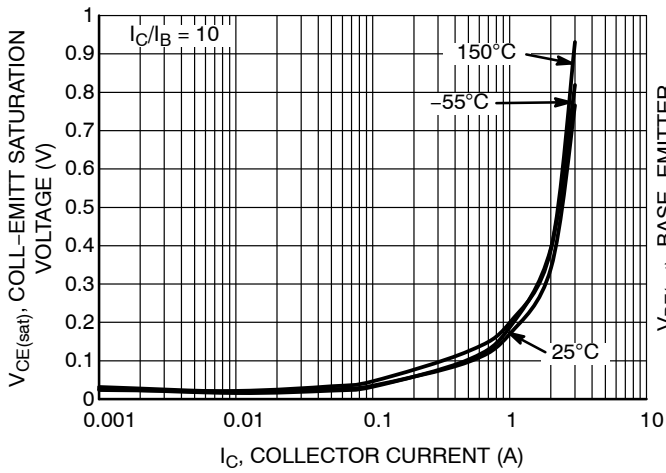


Figure 17. Collector-Emitter Saturation Voltage

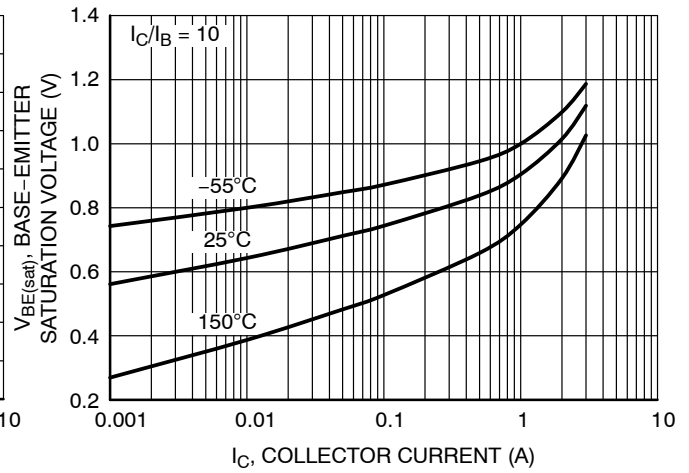


Figure 18. Base-Emitter Saturation Voltage

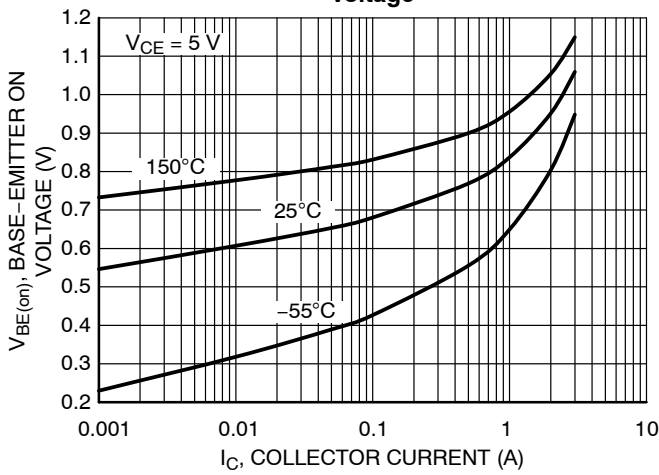


Figure 19. Base-Emitter "On" Voltage

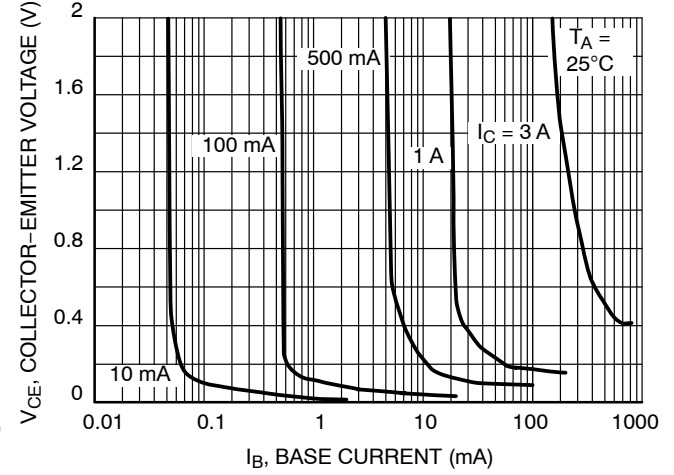


Figure 20. Collector Saturation Region

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,  
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

TYPICAL CHARACTERISTICS

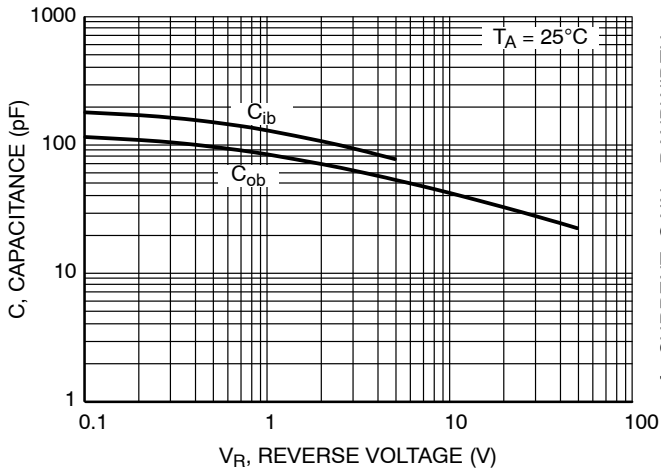


Figure 21. Capacitance

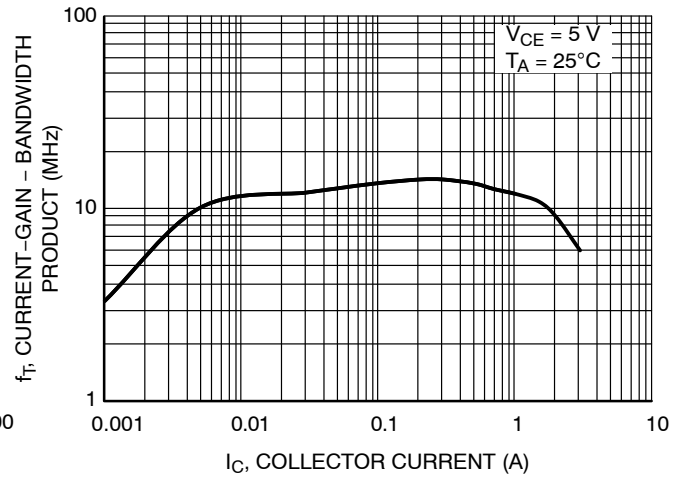


Figure 22. Current-Gain-Bandwidth Product

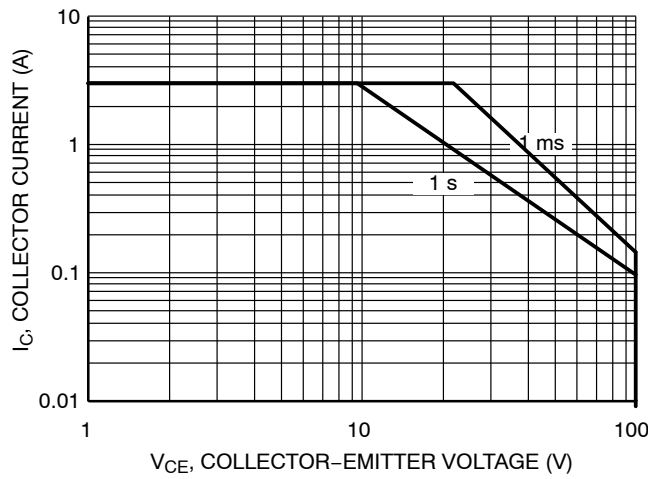


Figure 23. Safe Operating Area



**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G,  
MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

**ORDERING INFORMATION**

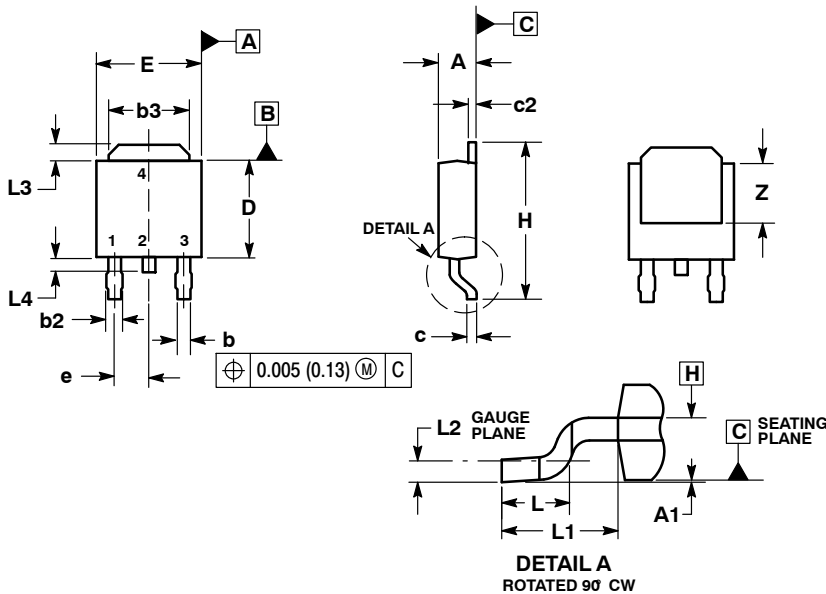
| Device       | Package Type        | Package | Shipping <sup>†</sup> |
|--------------|---------------------|---------|-----------------------|
| MJD31CG      | DPAK<br>(Pb-Free)   | 369C    | 75 Units / Rail       |
| MJD31C1G     | DPAK-3<br>(Pb-Free) | 369D    | 75 Units / Rail       |
| MJD31CRLG    | DPAK<br>(Pb-Free)   | 369C    | 1,800 Tape & Reel     |
| MJD31CT4G    | DPAK<br>(Pb-Free)   | 369C    | 2,500 Tape & Reel     |
| NJVMJD31CT4G | DPAK<br>(Pb-Free)   | 369C    | 2,500 Tape & Reel     |
| MJD31T4G     | DPAK<br>(Pb-Free)   | 369C    | 2,500 Tape & Reel     |
| NJVMJD31T4G  | DPAK<br>(Pb-Free)   | 369C    | 2,500 Tape & Reel     |
| MJD32CG      | DPAK<br>(Pb-Free)   | 369C    | 75 Units / Rail       |
| NJVMJD32CG   | DPAK<br>(Pb-Free)   | 369C    | 75 Units / Rail       |
| MJD32CRLG    | DPAK<br>(Pb-Free)   | 369C    | 1,800 Tape & Reel     |
| MJD32CT4     | DPAK                | 369C    | 2,500 Tape & Reel     |
| MJD32CT4G    | DPAK<br>(Pb-Free)   | 369C    | 2,500 Tape & Reel     |
| NJVMJD32CT4G | DPAK<br>(Pb-Free)   | 369C    | 2,500 Tape & Reel     |
| MJD32RLG     | DPAK<br>(Pb-Free)   | 369C    | 1,800 Tape & Reel     |
| MJD32T4G     | DPAK<br>(Pb-Free)   | 369C    | 2,500 Tape & Reel     |
| NJVMJD32T4G  | DPAK<br>(Pb-Free)   | 369C    | 2,500 Tape & Reel     |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)

PACKAGE DIMENSIONS

DPAK  
CASE 369C-01  
ISSUE D

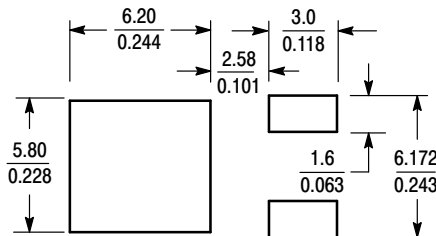


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

| DIM | INCHES    |       | MILLIMETERS |       |
|-----|-----------|-------|-------------|-------|
|     | MIN       | MAX   | MIN         | MAX   |
| A   | 0.086     | 0.094 | 2.18        | 2.38  |
| A1  | 0.000     | 0.005 | 0.00        | 0.13  |
| b   | 0.025     | 0.035 | 0.63        | 0.89  |
| b2  | 0.030     | 0.045 | 0.76        | 1.14  |
| b3  | 0.180     | 0.215 | 4.57        | 5.46  |
| c   | 0.018     | 0.024 | 0.46        | 0.61  |
| c2  | 0.018     | 0.024 | 0.46        | 0.61  |
| D   | 0.235     | 0.245 | 5.97        | 6.22  |
| E   | 0.250     | 0.265 | 6.35        | 6.73  |
| e   | 0.090 BSC |       | 2.29 BSC    |       |
| H   | 0.370     | 0.410 | 9.40        | 10.41 |
| L   | 0.055     | 0.070 | 1.40        | 1.78  |
| L1  | 0.108 REF |       | 2.74 REF    |       |
| L2  | 0.020 BSC |       | 0.51 BSC    |       |
| L3  | 0.035     | 0.050 | 0.89        | 1.27  |
| L4  | ---       | 0.040 | ---         | 1.01  |
| Z   | 0.155     | ---   | 3.93        | ---   |

SOLDERING FOOTPRINT\*



SCALE 3:1 (mm/inches)

STYLE 1:

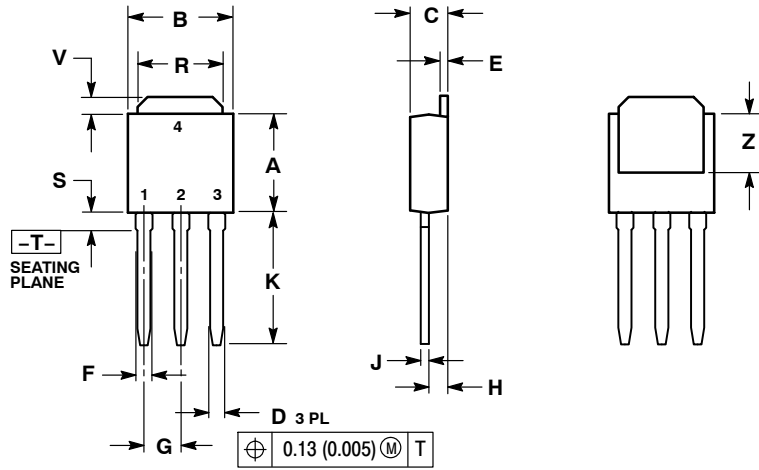
- PIN 1. BASE
- COLLECTOR
- EMITTER
- COLLECTOR

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**MJD31, NJVMJD31T4G, MJD31C, NJVMJD31CT4G (NPN), MJD32, NJVMJD32T4G, MJD32C, NJVMJD32CG, NJVMJD32CT4G (PNP)**

**PACKAGE DIMENSIONS**

**IPAK**  
CASE 369D-01  
ISSUE C



- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES    |       | MILLIMETERS |      |
|-----|-----------|-------|-------------|------|
|     | MIN       | MAX   | MIN         | MAX  |
| A   | 0.235     | 0.245 | 5.97        | 6.35 |
| B   | 0.250     | 0.265 | 6.35        | 6.73 |
| C   | 0.086     | 0.094 | 2.19        | 2.38 |
| D   | 0.027     | 0.035 | 0.69        | 0.88 |
| E   | 0.018     | 0.023 | 0.46        | 0.58 |
| F   | 0.037     | 0.045 | 0.94        | 1.14 |
| G   | 0.090 BSC |       | 2.29 BSC    |      |
| H   | 0.034     | 0.040 | 0.87        | 1.01 |
| J   | 0.018     | 0.023 | 0.46        | 0.58 |
| K   | 0.350     | 0.380 | 8.89        | 9.65 |
| R   | 0.180     | 0.215 | 4.45        | 5.45 |
| S   | 0.025     | 0.040 | 0.63        | 1.01 |
| V   | 0.035     | 0.050 | 0.89        | 1.27 |
| Z   | 0.155     | ---   | 3.93        | ---  |

- STYLE 1:  
PIN 1: BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

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